

WHAT IS CLAIMED IS:

1. A method for fabricating a thin film transistor liquid crystal display, which comprises the steps of:

- 5 forming a gate electrode on an insulating substrate;
 successively forming first and second insulating films
on the insulating substrate including the gate electrode,
the first insulating film being formed under first
deposition conditions including power, pressure and
10 electrode interval, the second insulating film being formed
under second deposition conditions where at least one of the
first deposition conditions is changed continuously over
time;
 successively forming first and second amorphous
15 silicon layers on the second insulating film to form an
active layer;
 successively forming an ohmic contact layer and a
source/drain electrode on the active layer; and
 forming a protective film on the resulting structure
20 including the source/drain electrode.

2. The method of Claim 1, wherein at least one of the
first deposition conditions for the first insulating film is
changed continuously over time until the second deposition

conditions of the second insulating film.

3. The method of Claim 2, wherein the electrode interval is changed continuously by regulation of the rotation speed of a motor, and the pressure is changed continuously by regulation of the pumping speed of a pump.

4. The method of Claim 2, wherein the electrode interval is changed continuously from 1,000 mils to 600 mils, and the pressure is changed continuously from 1,700 mTorr to 1,200 mTorr.

5. The method of Claim 1, wherein the first amorphous silicon layer is deposited under third deposition conditions including power, pressure and the interval between electrodes, and the second amorphous silicon layer is deposited under fourth deposition conditions where at least one of the third deposition conditions is changed continuously over time.

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6. The method of Claim 5, the power is changed continuously from 100 W to 600 W.

7. A method for fabricating a thin film transistor

liquid crystal display, which comprises the steps of:

forming a gate electrode on an insulating substrate;

successively forming first and second insulating films
on the insulating substrate including the gate electrode,
5 the first insulating film being formed under first
deposition conditions including power, pressure and
electrode interval, the second insulating film being formed
under second deposition conditions where at least one of the
first deposition conditions is changed continuously over
10 time;

successively forming first and second amorphous silicon
layers on the second insulating film, the first amorphous
silicon layer being formed under third deposition conditions
including power, pressure and electrode interval, the second
15 amorphous silicon layer being formed under fourth deposition
conditions where at least one of the third deposition
conditions is changed continuously over time;

successively forming an ohmic contact layer and a
source/drain electrode on the active layer; and

20 forming a protective film on the resulting structure
including the source/drain electrode.

8. The method of Claim 7, wherein the electrode
interval is changed continuously by regulation of the

rotation speed of a motor, and the pressure is changed continuously by regulation of the pumping speed of a pump.

9. The method of Claim 7, wherein the electrode
5 interval is continuously changed from 1,000 mils to 600 mils,
and the pressure is continuously changed from 1,700 mTorr to
1,200 mTorr.

10. The method of Claim 7, wherein the power is changed
10 continuously from 100W to 600 W.